



SWF7N70

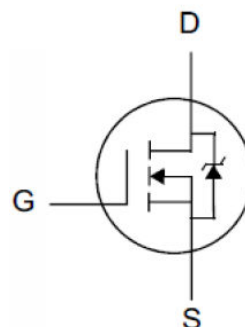
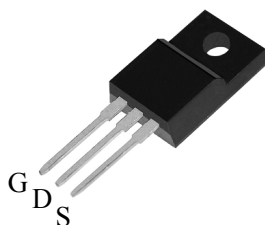
700V N-ch Planar MOSFET

General Features

- RoHS Compliant
- $R_{DS(ON),typ.}=1.34\ \Omega @ V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

Applications

- Adaptor
- Charger
- SMPS Standby Power



TO-220F

Package Not to Scale

Absolute Maximum Ratings

$T_C=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-to-Source Voltage	700	V
V_{GSS}	Gate-to-Source Voltage	± 30	
I_D	Continuous Drain Current	7.0	A
I_{DM}	Pulsed Drain Current at $V_{GS}=10V$	24	
E_{AS}	Single Pulse Avalanche Energy	330	mJ
P_D	Power Dissipation	35	W
	Derating Factor above $25^{\circ}C$	0.28	W/ $^{\circ}C$
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	$^{\circ}C$
$T_J \& T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3.57	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	



Electrical Characteristics

OFF Characteristics

 $T_J = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	700	--	--	V	$V_{GS}=0V$, $I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS}=700V$, $V_{GS}=0V$
		--	--	100		$V_{DS}=560V$, $V_{GS}=0V$, $T_J=125^{\circ}\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	$V_{GS}=+30V$, $V_{DS}=0V$
		--	--	-100		$V_{GS}=-30V$, $V_{DS}=0V$

ON Characteristics

 $T_J = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	1.34	1.55	Ω	$V_{GS}=10V$, $I_D=1.0A$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}$, $I_D=250\mu A$
gfs	Forward Transconductance	--	10	--	S	$V_{DS}=30V$, $I_D=3.0A$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	1100	--	pF	$V_{GS}=0V$, $V_{DS}=25V$, $f=1.0\text{MHz}$
C_{rss}	Reverse Transfer Capacitance	--	10	--		
C_{oss}	Output Capacitance	--	90	--		
Q_g	Total Gate Charge	--	20	--	nC	$V_{DD}=350V$, $I_D=7A$, $V_{GS}=0$ to $10V$
Q_{gs}	Gate-to-Source Charge	--	5	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	4.5	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	12	--	ns	$V_{DD}=350V$, $I_D=7A$, $V_{GS}=10V$ $R_g=4.7\Omega$
t_{rise}	Rise Time	--	10	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	18	--		
t_{fall}	Fall Time	--	10	--		

Source-Drain Body Diode Characteristics

 $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current ^[2]	--	--	7.0	A	Integral pn-diode in MOSFET
I_{SM}	Pulsed Source Current ^[2]	--	--	24		
V_{SD}	Diode Forward Voltage	--	--	1.5	V	$I_S=7A$, $V_{GS}=0V$
t_{rr}	Reverse Recovery Time	--	320	--	ns	$V_{GS}=0V$ $I_F=7A$, $di/dt=100A/\mu s$
Q_{rr}	Reverse Recovery Charge	--	0.9	--	μC	



Typical Characteristics

Figure 1. Maximum Transient Thermal Impedance

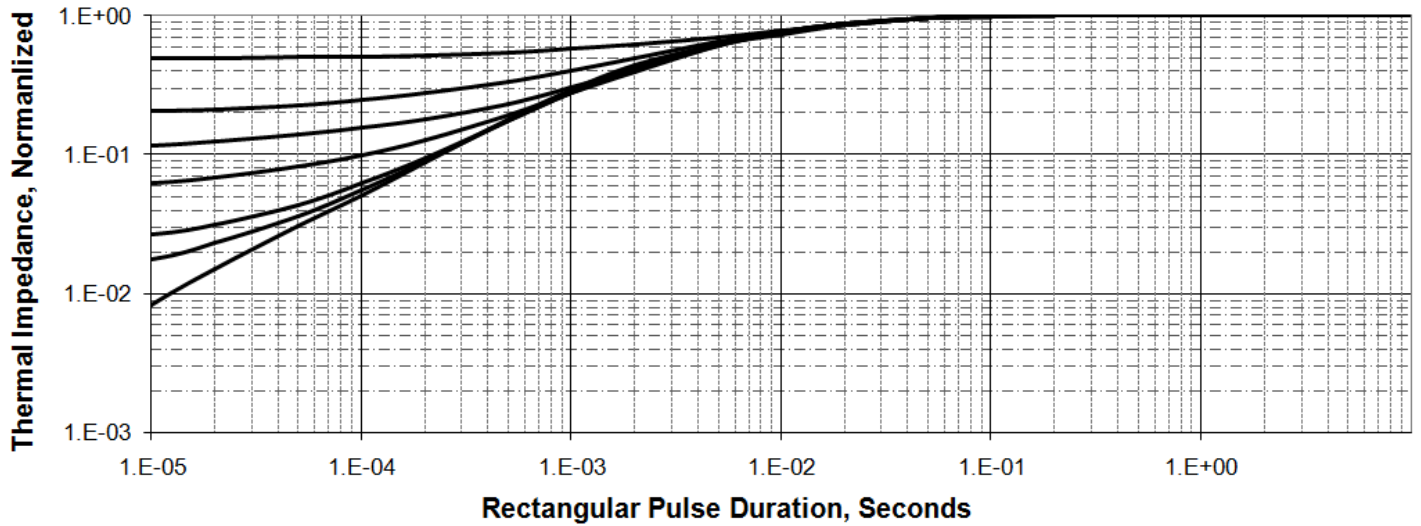


Figure 2 . Max. Power Dissipation vs Case Temperature

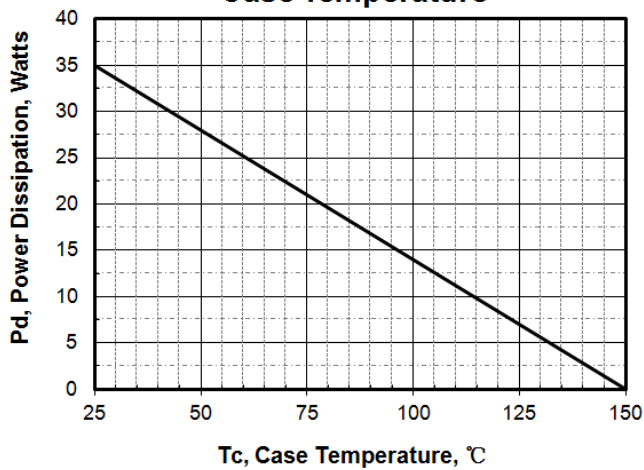


Figure 3 .Maximum Continuous Drain Current vs T_c

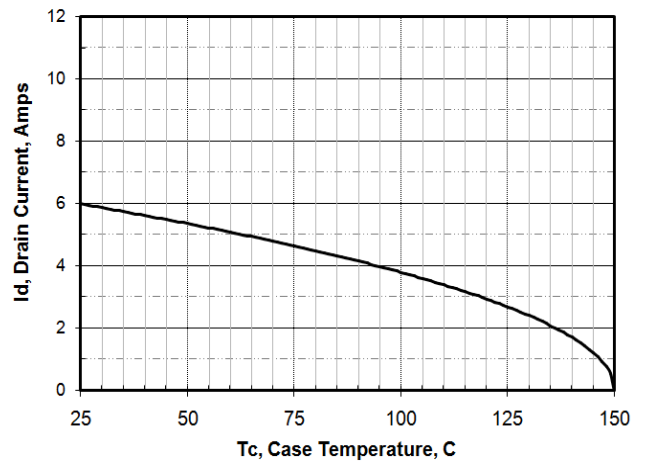


Figure 4. Output Characteristics

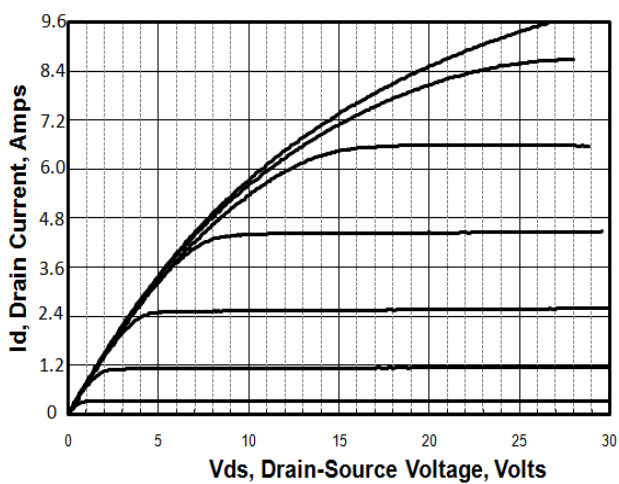
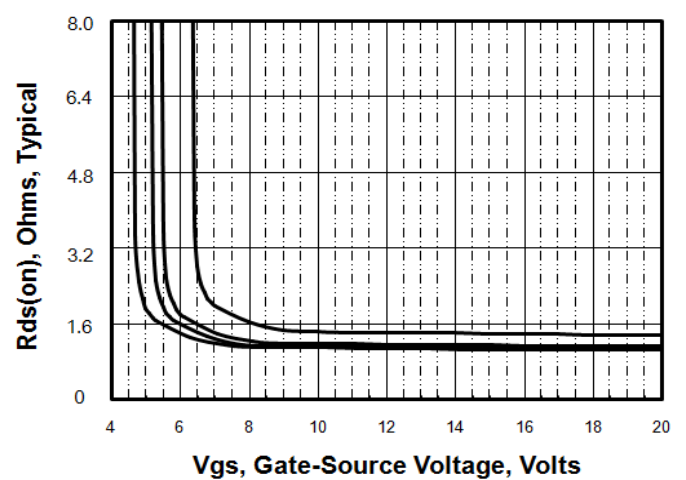


Figure 5. $R_{ds(on)}$ vs Gate Voltage





Typical Characteristics(Cont.)

Figure 6. Peak Current Capability

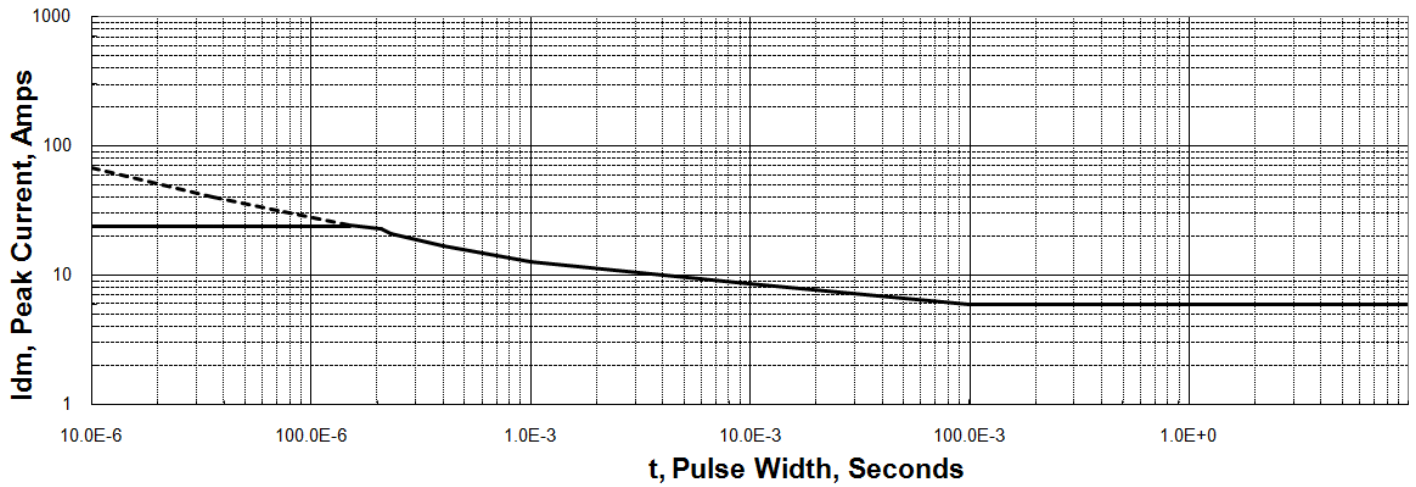


Figure 7. Transfer Characteristics

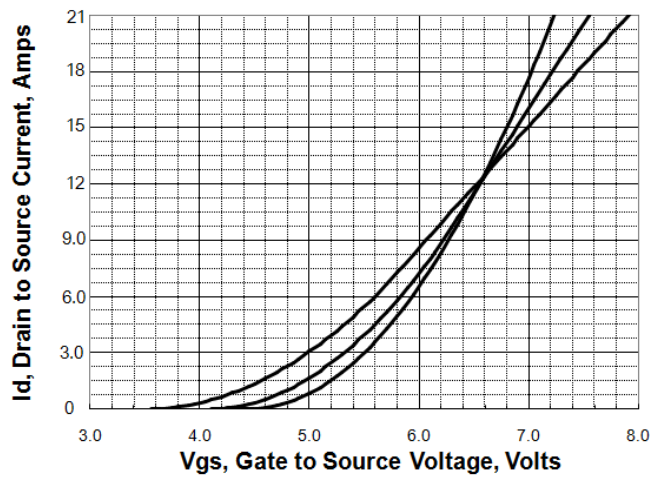


Figure 8. Unclamped Inductive Switching Capability

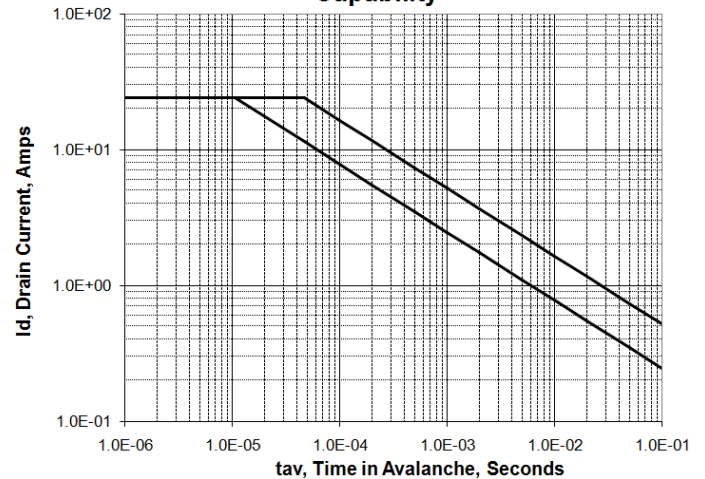


Figure 9. Drain to Source ON Resistance vs Drain Current

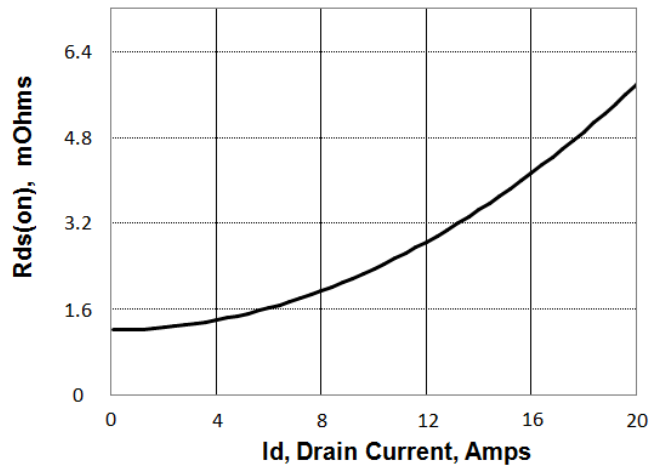
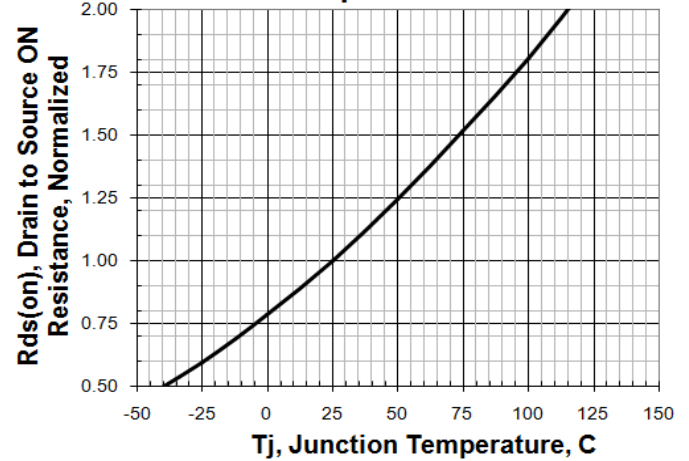


Figure 10. $R_{ds(on)}$ vs Junction Temperature



Typical Characteristics(Cont.)

Figure 11. Breakdown Voltage vs Temperature

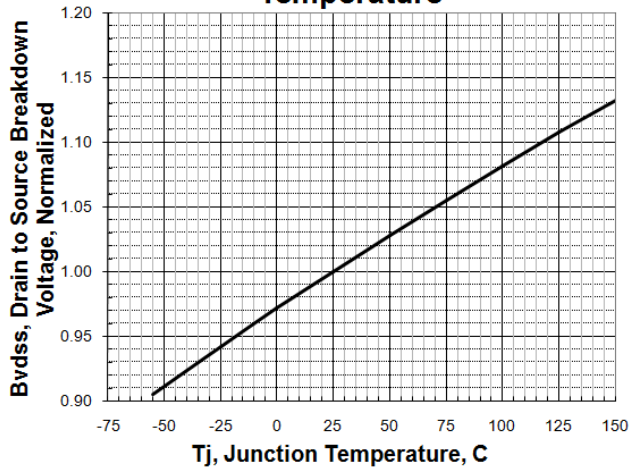


Figure 12. Threshold Voltage vs Temperature

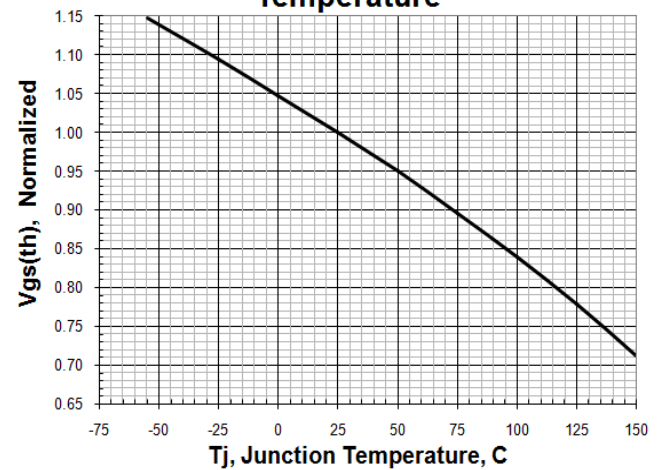


Figure 13 . Maximum Safe Operating Area

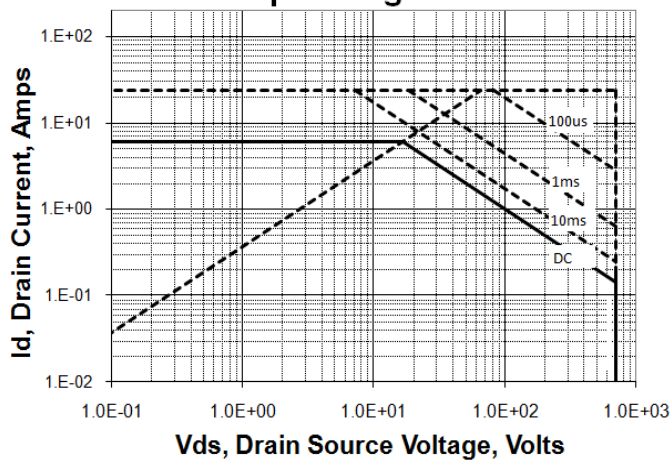


Figure 14. Capacitance vs Vds

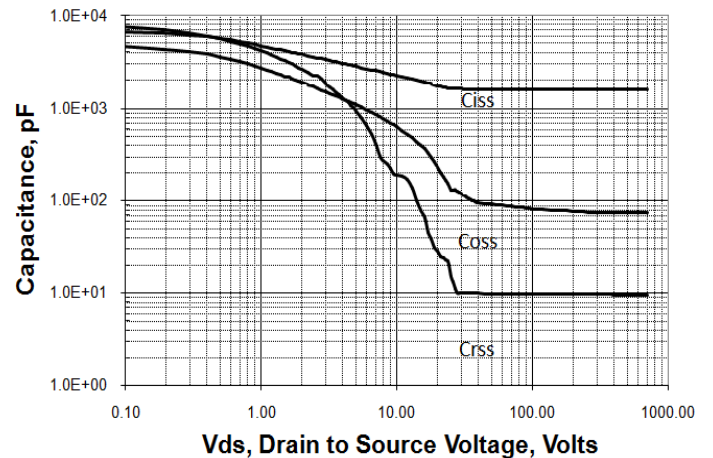


Figure 15 . Typical Gate Charge

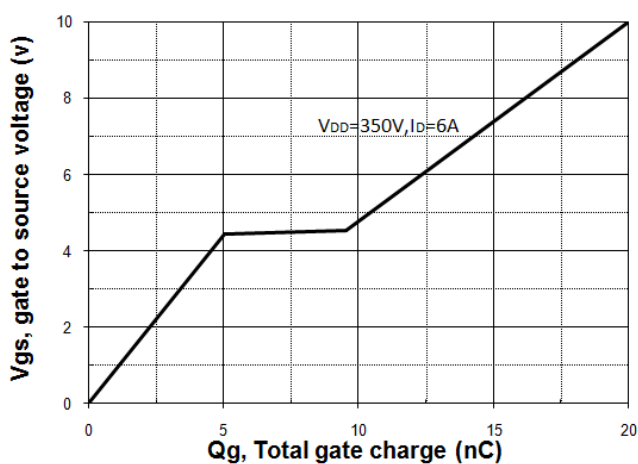
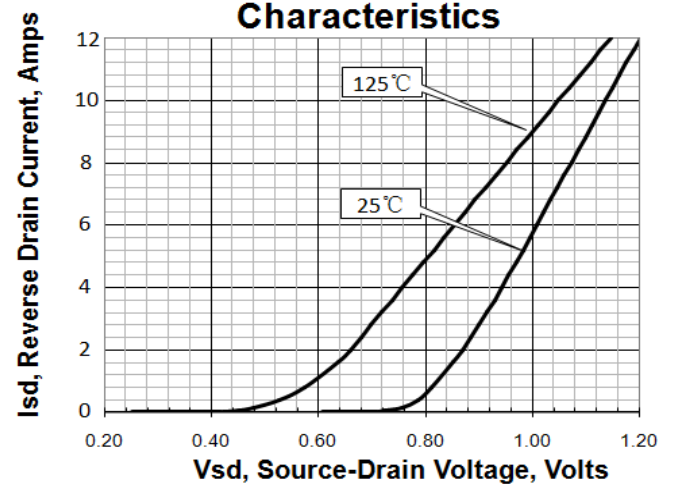


Figure 16. Body Diode Transfer Characteristics



Test Circuits and Waveforms

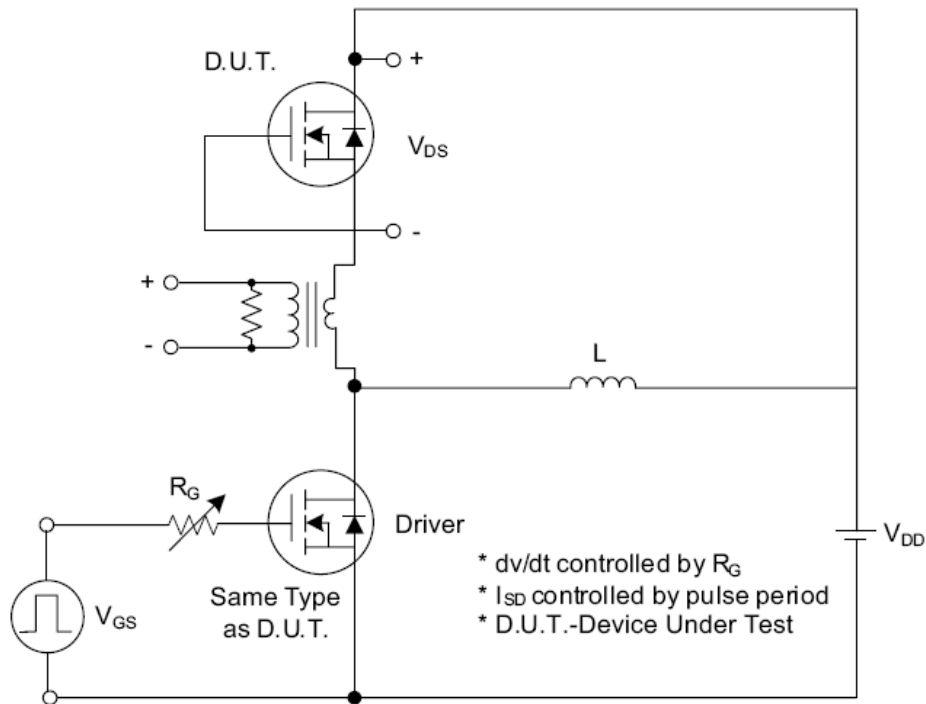


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

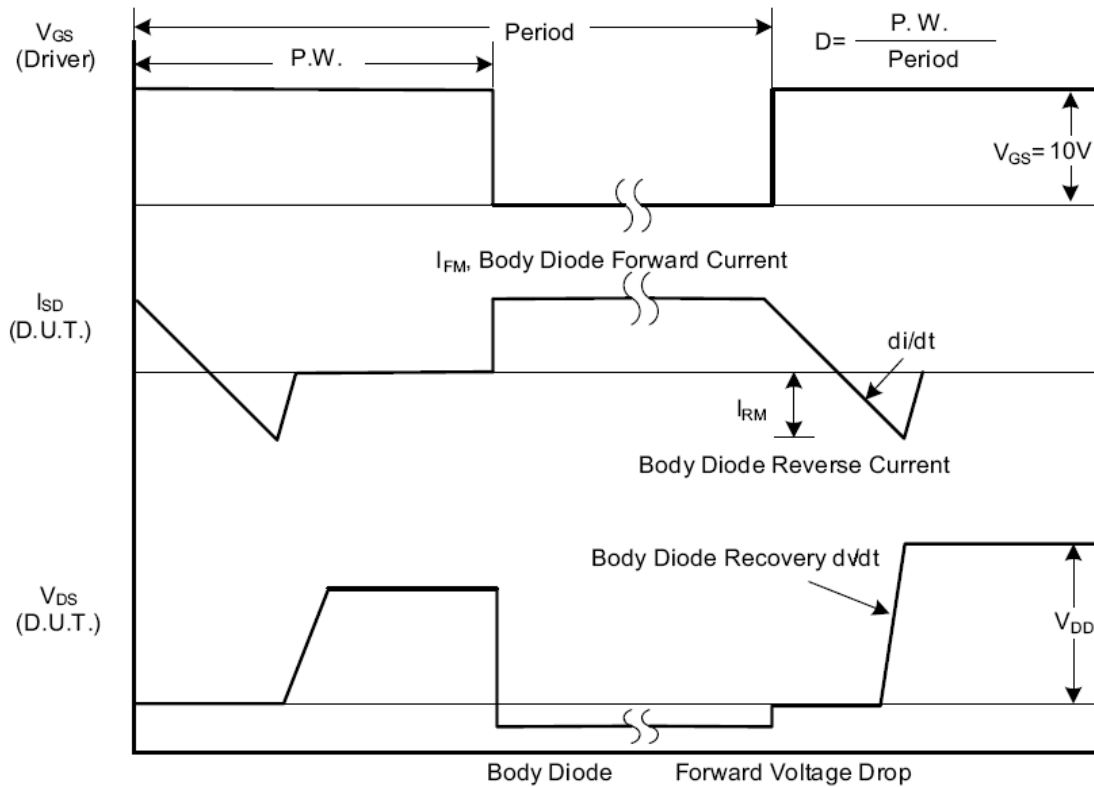


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

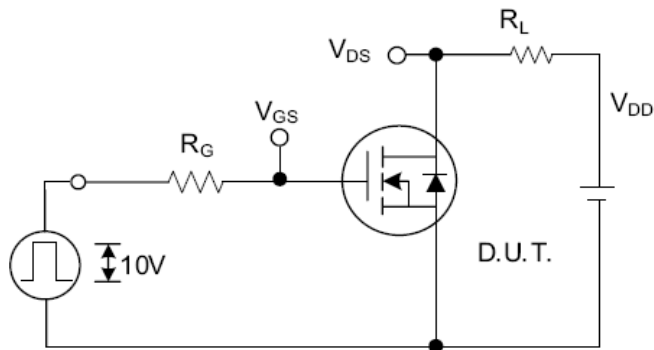


Fig. 2.1 Switching Test Circuit

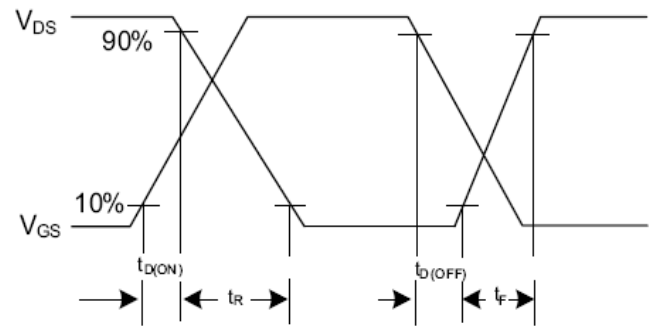


Fig. 2.2 Switching Waveforms

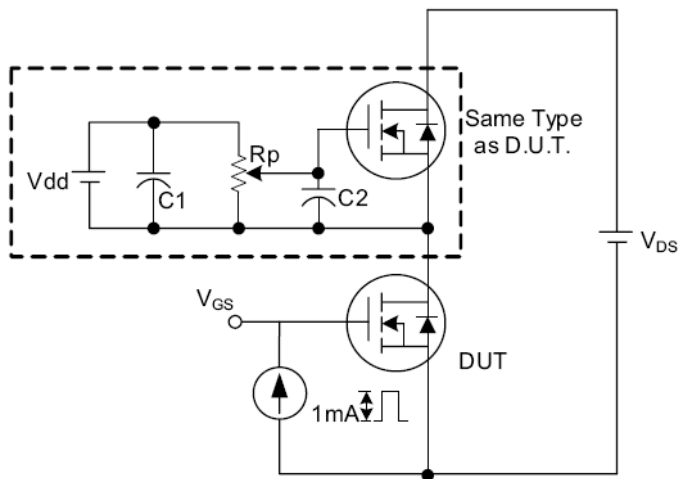


Fig. 3.1 Gate Charge Test Circuit

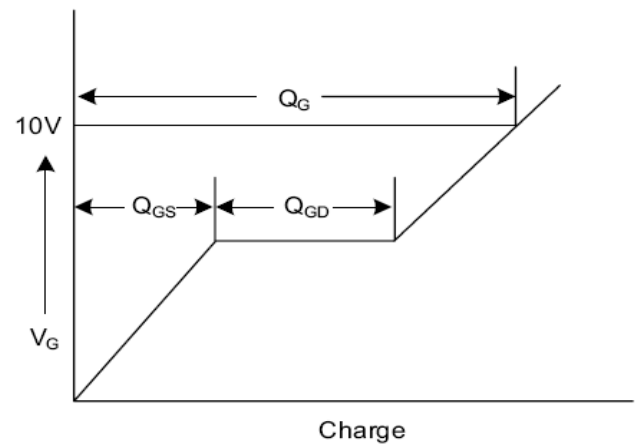


Fig. 3.2 Gate Charge Waveform

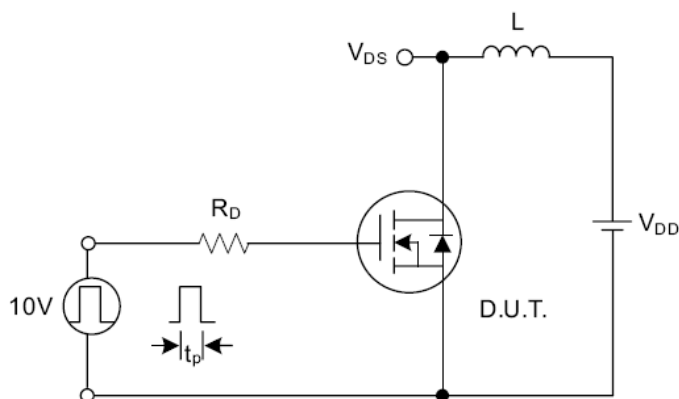


Fig. 4.1 Unclamped Inductive Switching Test Circuit

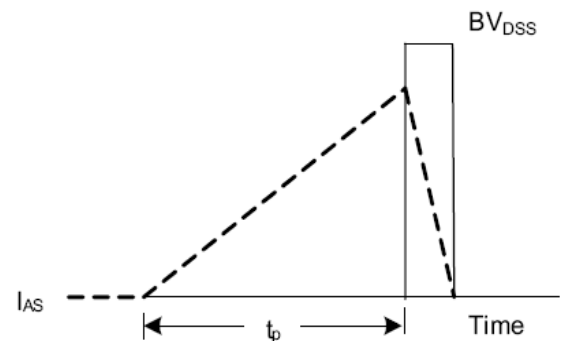
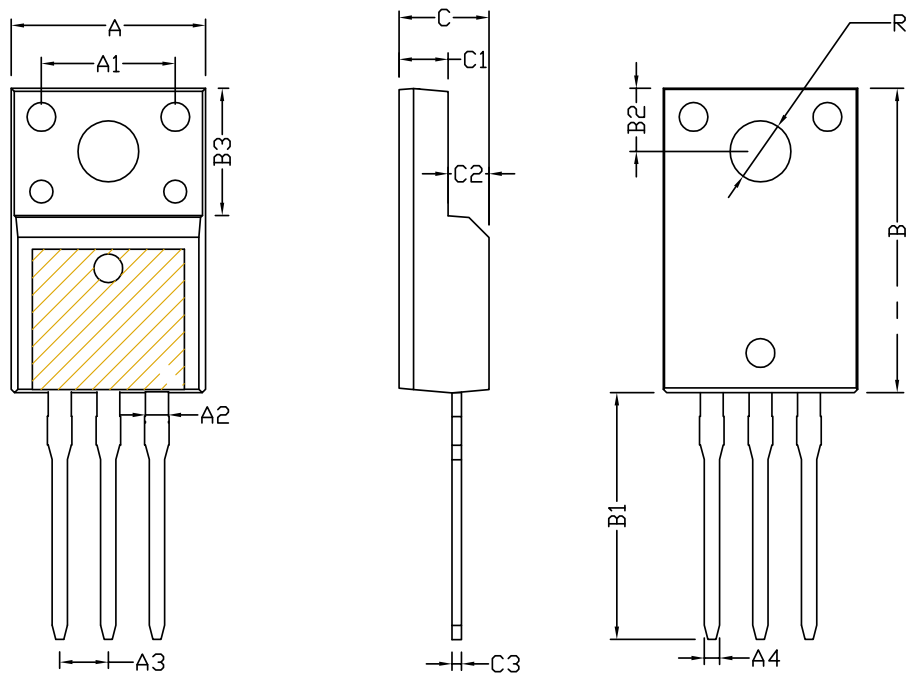


Fig. 4.2 Unclamped Inductive Switching Waveforms



Package Mechanical Data(TO-220F)



标注	最小	标准	最大	标注	最小	标准	最大	标注	最小	标准	最大
A	10.03	10.13	10.23	B	15.81	15.91	16.01	C	4.62	4.7	4.78
A1	6.5	7.0	7.5	B1	12.79	12.89	12.99	C1	2.5	2.55	2.6
A2	1.20	1.28	1.36	B2	3.0	3.3	3.6	C2	2.1	2.15	2.2
A3		2.54		B3	6.6	6.65	6.7	C3		0.5	
A4	0.7	0.8	0.9	R		3.18					